

CLAIMS

What is claimed is:

1. A multi-layer substrate, comprising:

- 5 a. a low glass transition temperature polyimide layer
comprising a polyimide base polymer synthesized by
contacting an aromatic dianhydride with a diamine
component, the diamine component comprising about 50
to about 90 mole % aliphatic diamine and about 10 to
10 about 50 mole % aromatic diamine, said polyimide base
polymer having a glass transition temperature from about
150, 160, 170, 180, or 185 to about 190, 195, 197 or
200°C;
 - b. a high glass transition temperature polyimide layer having
a glass transition temperature above the low glass
15 transition temperature polyimide layer; and
 - c. a conductive layer,
- wherein the high glass transition temperature polyimide layer is
between the conductive layer and the low glass transition polyimide
layer.

20 2. A multi-layer substrate in accordance with Claim 1 further
comprising a second low glass transition temperature polyimide layer
located between the conductive layer and the high glass transition
temperature polyimide layer.

25 3. A multi-layer substrate in accordance with Claim 1 wherein the
conductive layer is between a first and a second low glass temperature
polyimide layer, wherein a high glass transition temperature polyimide
layer is adjacent to the first low glass transition temperature polyimide
layer and wherein a high glass transition temperature polyimide layer is
adjacent to the second low glass transition temperature polyimide layer.

30 4. A multi-layer substrate in accordance with Claim 1, wherein:
i. the aliphatic diamine has the structural formula $H_2N-R_1-NH_2$, where R_1
is a substituted or unsubstituted hydrocarbon from C_4 to C_{16} ; and ii. the
polyimide base polymer is further defined as having a z-axis coefficient of
thermal expansion of less than 80, 85, 90, 95, 100, 105, 110, 115, 120,
35 125, 130, 135, 140, 145, or 150 ppm/°C according to ASTM Method IPC-
650 2.4.41.

5. A multi-layer substrate in accordance with Claim 1, wherein the aliphatic diamine has the structural formula $H_2N-R_2-NH_2$, where R_2 is a hydrocarbon from C_6 to C_8 .

6. A multi-layer substrate in accordance with Claim 1, wherein the aliphatic diamine is selected from the group comprising 1,4-tetramethylenediamine, 1,5-pentamethylenediamine (PMD), 1,7-heptamethylene diamine, 1,8-octamethylenediamine, 1,9-nonamethylenediamine, 1,10-decamethylenediamine (DMD), 1,11-undecamethylenediamine, 1,12-dodecamethylenediamine (DDD), and 1,16-hexadecamethylenediamine.

7. A multi-layer substrate in accordance with Claim 1, wherein the aromatic diamine is selected from the group comprising 1,2-bis-(4-aminophenoxy) benzene, 1,3-bis-(4-aminophenoxy) benzene, 1,2-bis-(3-aminophenoxy)benzene, 1,3-bis-(3-aminophenoxy) benzene, 1-(4-aminophenoxy)-3-(3-aminophenoxy) benzene, 1,4-bis-(4-aminophenoxy) benzene, 1,4-bis-(3-aminophenoxy) benzene, and (4-aminophenoxy)-4-(3-aminophenoxy) benzene, 2,2-bis-(4-[4-aminophenoxy]phenyl) propane (BAPP), and 2,5-dimethyl-1,4-phenylenediamine (DPX).

8. A multi-layer substrate in accordance with Claim 1, wherein the aromatic dianhydride is selected from the group comprising 2,2',3,3'-benzophenone tetracarboxylic dianhydride, 2,3,3',4'-benzophenone tetracarboxylic dianhydride, 3,3',4,4'-benzophenone tetracarboxylic dianhydride (BTDA), 2,2',3,3'-biphenyl tetracarboxylic dianhydride, 2,3,3',4'-biphenyl tetracarboxylic dianhydride, 3,3',4,4'-biphenyl tetracarboxylic dianhydride (BPDA), 4,4'-oxydiphthalic anhydride (ODPA), 2,2-bis-(3,4-dicarboxyphenyl) 1,1,1,3,3,3,-hexafluoropropane dianhydride (6FDA), pyromellitic dianhydride (PMDA), and tetrahydrofuran tetracarboxylic dianhydride.

9. A multi-layer substrate in accordance with Claim 1, wherein the aliphatic diamine is hexamethylene diamine (HMD), wherein the aromatic diamine is 1,3-bis-(4-aminophenoxy) benzene, and wherein the aromatic dianhydride is a combination of 3,3',4,4'-benzophenone tetracarboxylic dianhydride (BTDA) and 3,3',4,4'-biphenyl tetracarboxylic dianhydride (BPDA).

10. A multi-layer substrate in accordance with Claim 1, wherein the aromatic dianhydride component is 70 to 95 mole % 3,3',4,4'-biphenyltetracarboxylic dianhydride (BPDA) and 5 to 30 mole % 3,3',4,4'-benzophenonetetracarboxylic dianhydride (BTDA), and wherein the

diamine component is 60 to 80 mole % hexamethylene diamine (HMD) and 20 to 40 mole % 1,3-bis-(4-aminophenoxy) benzene (APB-134, RODA).

11. A multi-layer substrate in accordance with Claim 1, wherein a
5 surface of the conductive layer is in direct contact with the high glass transition temperature polyimide layer.

12. A multi-layer substrate in accordance with Claim 9, wherein a surface of the low glass transition temperature polyimide layer is in direct contact with the high glass transition temperature polyimide layer.

10 13. A multi-layer substrate in accordance with Claim 1, further comprising one or more additional conductive layers.

14. A multi-layer substrate having a first and second outer layer, in accordance with Claim 11, wherein at least one of the additional conductive layers is located within the multi-layer substrate, between the
15 first and second outer layer and being in contact with a conductive pathway extending through at least one of said polyimide layers.

15. A multi-layer substrate in accordance with Claim 1, wherein the substrate is at least: i. a component of; or ii. a precursor to, a packaging composition, the packaging composition being a chip on lead ("COL")
20 package, a chip on flex ("COF") package, a lead on chip ("LOC") package, a multi-chip module ("MCM") package, a ball grid array ("BGA" or "μ-BGA") package, chip scale package ("CSP"), a tape automated bonding ("TAB") package, or a package comprising a micro-via.

16. A multi-layer substrate in accordance with Claim 1, wherein the
25 substrate is a component of a wafer level integrated circuit packaging comprising a conductive passageway, said conductive passageway being at least a portion of one or more members of the group consisting of: a wire bond, a conductive metal, and a solder bump.

17. A multi-layer substrate in accordance with Claim 1 further
30 comprising a filler material selected from the group consisting of alumina, silica, boron nitride, silicon carbide, clay, diamond, dicalcium phosphate, aluminum nitride, titanium dioxide, polyaniline, polythiophene, polypyrrole, polyphenylenevinylene, polydialkylfluorenes, carbon black, and graphite.

18. A multi-layer substrate in accordance with Claim 1, wherein the
35 difference in lamination temperature between the high T_g polyimide layer and the low T_g polyimide layer is in a range between and including any two of the following (in °C): 10, 15, 20, 25, 30, 35, 40, 45, 50, 75, 100, 125, 150, 175, and 200 °C.

19. A sequential build-up (SBU) micro-via integrated circuit packaging substrate, comprising:

- 5 a) a first layer, the first layer comprising a low glass transition temperature polyimide layer comprising a polyimide base polymer synthesized by contacting an aromatic dianhydride with a diamine component, the diamine component comprising about 50 to about 90 mole % aliphatic diamine and about 10 to about 50 mole % aromatic diamine, said polyimide base polymer having a
10 glass transition temperature from about 150, 160, 170, 180, or 185 to about 190, 195, 197 or 200°C;
- 15 (b) a second layer, the second layer comprising a high glass transition temperature polyimide layer having a glass transition temperature above the low glass transition temperature polyimide layer; and
- c) a pre-circuitized organic core material having a plurality of laser induced microvias of 10-100 μm in diameter;

wherein at least one surface of the core material is bonded to at least one surface of either the first layer or the second layer, said microvia
20 extending from the core material into or through said first layer or said second layer.